

2SD1368

Silicon NPN Epitaxial

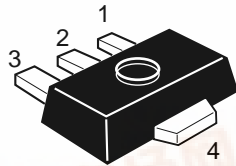
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Application

- Low frequency power amplifier
- Complementary pair with 2SB1002

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

2SD1368

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
Collector peak current	$i_{C(peak)}^{*1}$	1.5	A
Collector power dissipation	P_C^{*2}	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10$ ms, Duty cycle $\leq 20\%$

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

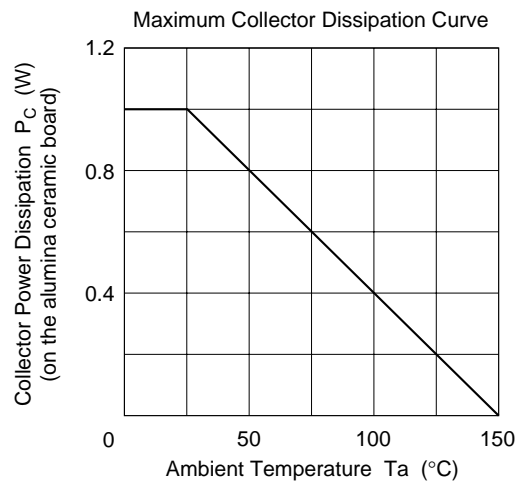
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 80$ V, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4$ V, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500		$V_{CE} = 2$ V, $I_C = 0.1$ A
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 1$ A, $I_B = 0.1$ A, Pulse
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.2	V	$I_C = 1$ A, $I_B = 0.1$ A, Pulse
Gain bandwidth product	f_T	—	100	—	MHz	$V_{CE} = 2$ V, $I_C = 10$ mA, Pulse
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10$ V, $I_E = 0$, $f = 1$ MHz

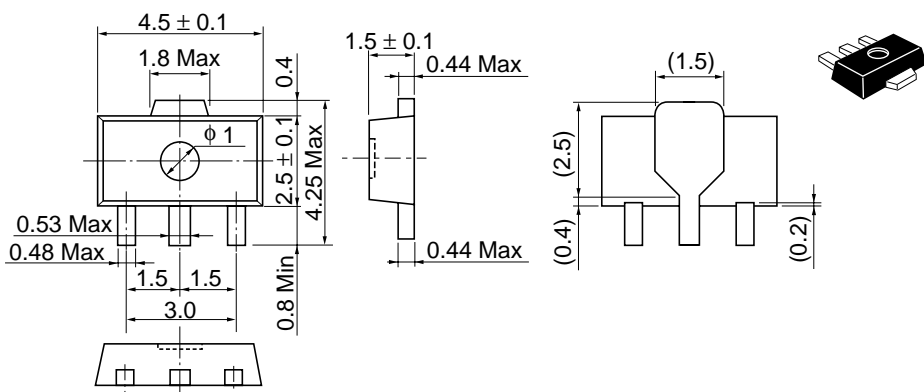
Note: 1. The 2SD1368 is grouped by h_{FE} as follows.

Mark	CA	CB	CC
h_{FE}	100 to 200	160 to 200	250 to 500

See characteristic curves of 2SD789.



Unit: mm



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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL NorthAmerica : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher StraÙe 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX